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25. (Amended) The semiconductor device of claim *23*, further comprising a layer of [oxide] reoxidation on the spacer and the oxide [active area] layer, the layer of [oxide] reoxidation being formed by a polycide reoxidation and forming a smile effect at the boundary between the feature and the oxide [active area] layer.

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Contd
26. (Amended) An electronic device comprising:

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a first layer of oxide;
a feature over the first layer of oxide, the feature having a surface;
a boundary between the first layer of oxide and the feature; and
a spacer comprising silicon nitride or an amorphous silicon film only on the surface of the feature.

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28. (Amended) The electronic device of claim *26* wherein:
the first layer of oxide comprises a layer of gate oxide;
the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;
[the spacer comprises silicon nitride or an amorphous silicon film;] and
the surface of the feature comprises sidewalls of the electrode.

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29. (Amended) The electronic device of claim *26*, further comprising a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile effect at the boundary between the feature and the first layer of oxide.

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30. (Amended) An electronic device comprising:
a first layer of oxide;
a feature over the first layer of oxide, the feature having a surface;
a boundary between the first layer of oxide and the feature;
a spacer comprising silicon nitride or an amorphous silicon film only on the surface of the feature; and

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a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile effect at the boundary between the feature and the first layer of oxide.

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10 34. (Amended) The electronic device of claim 30 wherein:

the first layer of oxide comprises a layer of gate oxide;

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

the spacer [comprises silicon nitride or an amorphous silicon film and the spacer] is deposited on the surface of the feature extending to and terminating at the boundary; and

the surface of the feature comprises sidewalls of the electrode.

10 36. (Amended) An electronic device comprising:

a first layer of oxide;

an electrode on the first layer of oxide, the electrode having sidewalls; and

a spacer comprising silicon nitride or an amorphous silicon film deposited only on the sidewalls of the electrode, the spacer extending to and terminating at a boundary between the first layer of oxide and the sidewalls of the electrode.

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10 37. (Amended) The electronic device of claim 36 wherein:

the first layer of oxide comprises a layer of gate oxide; and

the electrode comprises polysilicon, a refractory metal, and a dielectric, or undoped silicon[; and]

the spacer comprises silicon nitride or an amorphous silicon film].

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10 38. (Amended) The electronic device of claim 36, further comprising a second layer of oxide on the spacer and the first layer of oxide, the second layer of oxide forming a smile effect at the boundary between the first layer of oxide and the sidewalls of the electrode.

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10 39. (Amended) A semiconductor device, comprising:

a first layer of oxide;

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a feature protruding from the first layer of oxide and having sidewalls, the feature including:

• a polysilicon portion;
a portion of conductive material deposited on the polysilicon portion; and
a spacer comprising silicon nitride or an amorphous silicon film selectively deposited only on the sidewalls of the feature; and

a second layer of oxide deposited on the semiconductor device, wherein the spacer is interposed between the second layer of oxide and the sidewalls of the feature.

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40. (Amended) The semiconductor device of claim 19, wherein [the spacer comprises silicon nitride or an amorphous silicon film and] the portion of conductive material comprises tungsten silicide.

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42. (Amended) A gate electrode, comprising:

one or more layers of conductive materials etched to form a feature having sidewalls exposing the layers;

a selectively deposited spacer comprising silicon nitride or an amorphous silicon film, wherein the spacer is deposited only on the sidewalls of the feature;

a layer of oxide disposed over the gate electrode.

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43. (Amended) The gate electrode of claim 42, wherein the layers of conductive materials comprise tungsten silicide [and the selectively deposited spacer comprises silicon nitride or an amorphous silicon film].

Please add the following new claim:

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44. (New)

An electronic device comprising:

a first layer of oxide;

an electrode on the first layer of oxide, the electrode having sidewalls; and

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